

## HIGH EFFICIENCY ULTRAFAST DIODE

### MAIN PRODUCT CHARACTERISTICS

|                |              |
|----------------|--------------|
| $I_{F(AV)}$    | Up to 2 x 8A |
| $V_{RRM}$      | 200 V        |
| $T_j (max)$    | 175 °C       |
| $V_F (typ)$    | 0.78 V       |
| $t_{rr} (typ)$ | 20 ns        |

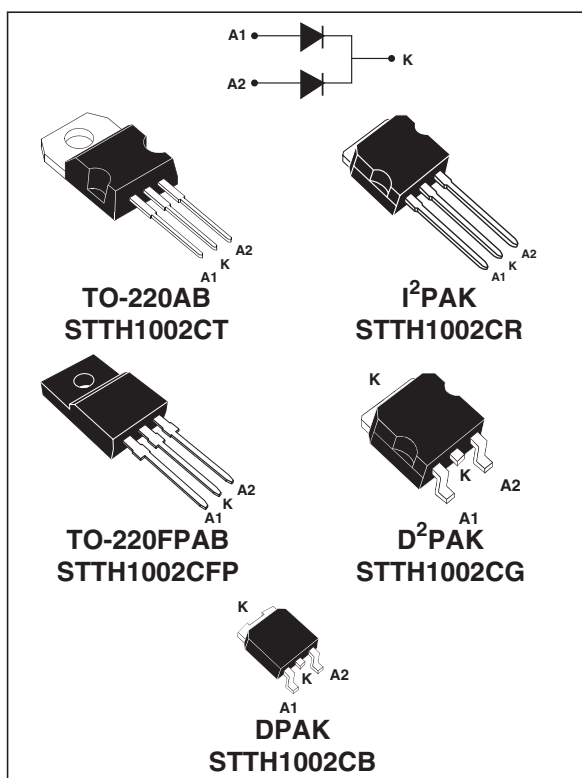
### FEATURES AND BENEFITS

- Suited for SMPS
- Low losses
- Low forward and reverse recovery times
- Insulated package: TO-220FPAB
- High junction temperature
- Low leakage current

### DESCRIPTION

Dual center tap rectifier suited for Switch Mode Power Supplies and High frequency DC to DC converters.

Packaged in DPAK, D<sup>2</sup>PAK, TO-220AB, TO220-FPAB and I<sup>2</sup>PAK, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



### ABSOLUTE RATINGS (limiting values, per diode)

| Symbol       | Parameter                              |                                                                   |            |            | Value | Unit          |
|--------------|----------------------------------------|-------------------------------------------------------------------|------------|------------|-------|---------------|
| $V_{RRM}$    | Repetitive peak reverse voltage        |                                                                   |            |            | 200   | V             |
| $I_{F(RMS)}$ | RMS forward current                    | TO-220AB / TO-220FPAB / I <sup>2</sup> PAK / D <sup>2</sup> PAK / |            |            | 20    | A             |
|              |                                        | DPAK                                                              |            |            | 10    |               |
| $I_{F(AV)}$  | Average forward current $\delta = 0.5$ | TO-220AB / I <sup>2</sup> PAK / D <sup>2</sup> PAK / DPAK         | Tc = 155°C | Per diode  | 5     | A             |
|              |                                        |                                                                   | Tc = 150°C | Per device | 10    |               |
|              |                                        |                                                                   | Tc = 135°C | Per diode  | 8     |               |
|              |                                        |                                                                   | Tc = 125°C | Per device | 16    |               |
|              |                                        | TO-220FPAB                                                        | Tc = 140°C | Per diode  | 5     |               |
|              |                                        |                                                                   | Tc = 120°C | Per device | 10    |               |
|              |                                        |                                                                   | Tc = 110°C | Per diode  | 8     |               |
|              |                                        |                                                                   | Tc = 75°C  | Per device | 16    |               |
| $I_{FSM}$    | Surge non repetitive forward current   | tp = 10 ms Sinusoidal                                             |            |            | 50    | A             |
| $T_{stg}$    | Storage temperature range              |                                                                   |            |            |       | - 65 + 175 °C |
| $T_j$        | Maximum operating junction temperature |                                                                   |            |            |       | 175 °C        |

## STTH1002C

### THERMAL PARAMETERS

| Symbol        | Parameter        |                                                           |            | Maximum | Unit |
|---------------|------------------|-----------------------------------------------------------|------------|---------|------|
| $R_{th(j-c)}$ | Junction to case | TO-220AB / I <sup>2</sup> PAK / D <sup>2</sup> PAK / DPAK | Per diode  | 4.0     | °C/W |
|               |                  |                                                           | Per device | 2.5     |      |
|               |                  | TO-220FPAB                                                | Per diode  | 6.5     |      |
|               |                  |                                                           | Per device | 5       |      |
| $R_{th(j-c)}$ | Coupling         | TO-220AB / I <sup>2</sup> PAK / D <sup>2</sup> PAK / DPAK |            | 1.0     | °C/W |
|               |                  | TO-220FPAB                                                |            | 3.5     |      |

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode1}) = P(\text{diode1}) \times R_{th(j-c)} (\text{per diode}) + P(\text{diode2}) \times R_{th(c)}$$

### STATIC ELECTRICAL CHARACTERISTICS (per diode)

| Symbol     | Parameter               | Tests conditions          |                     | Min. | Typ. | Max. | Unit          |
|------------|-------------------------|---------------------------|---------------------|------|------|------|---------------|
| $I_R^*$    | Reverse leakage current | $T_j = 25^\circ\text{C}$  | $V_R = V_{RRM}$     |      |      | 5    | $\mu\text{A}$ |
|            |                         | $T_j = 125^\circ\text{C}$ |                     |      | 3    | 40   |               |
| $V_F^{**}$ | Forward voltage drop    | $T_j = 25^\circ\text{C}$  | $I_F = 5\text{ A}$  |      |      | 1.1  | V             |
|            |                         | $T_j = 25^\circ\text{C}$  | $I_F = 10\text{ A}$ |      |      | 1.25 |               |
|            |                         | $T_j = 150^\circ\text{C}$ | $I_F = 5\text{ A}$  |      | 0.78 | 0.89 |               |
|            |                         | $T_j = 150^\circ\text{C}$ | $I_F = 10\text{ A}$ |      |      | 1.05 |               |

Pulse test: \*  $t_p = 5\text{ms}$ ,  $\delta < 2\%$

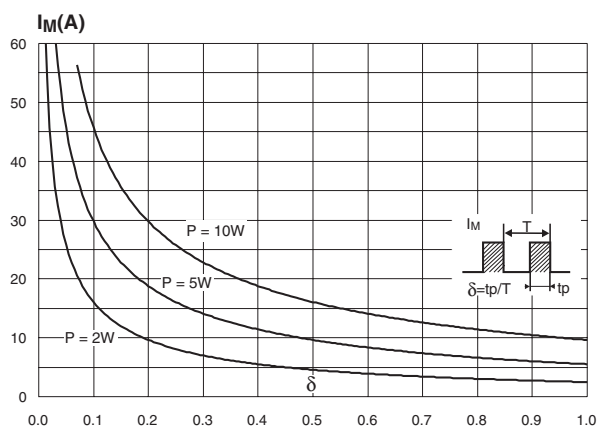
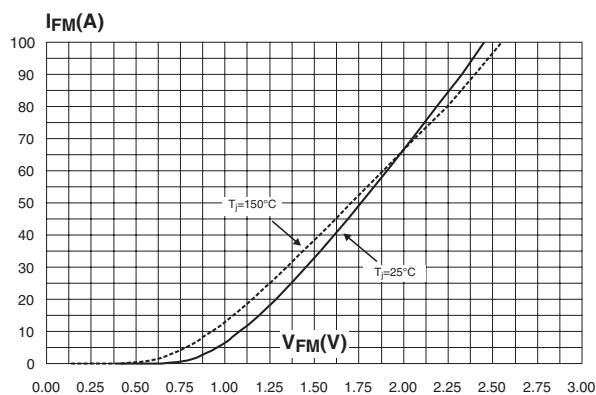
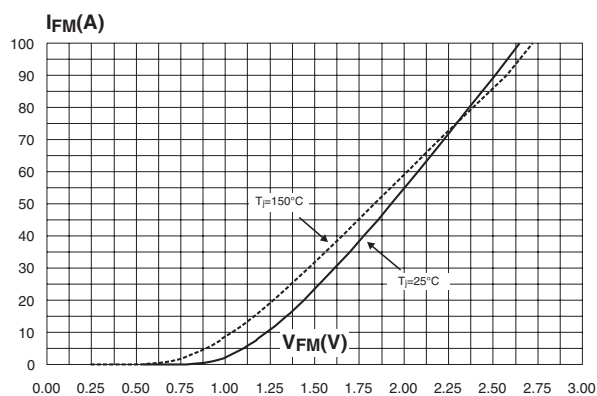
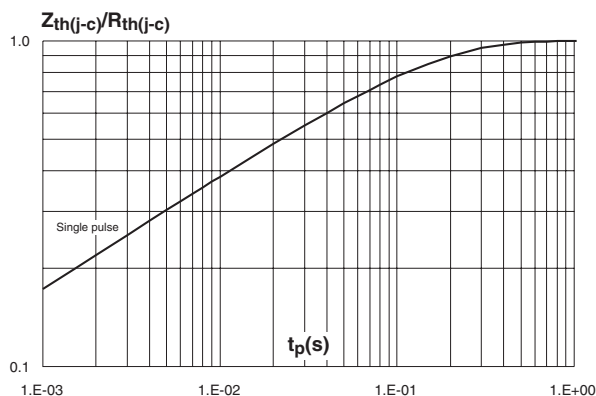
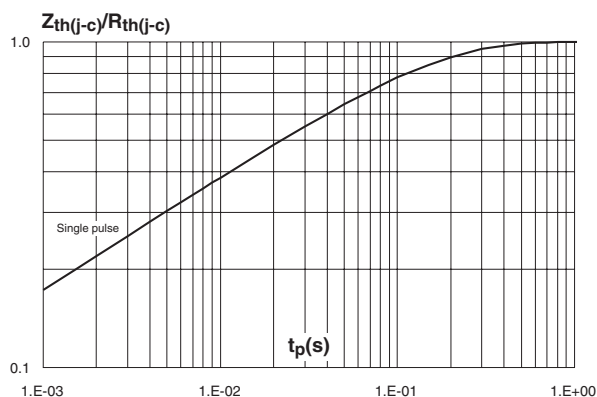
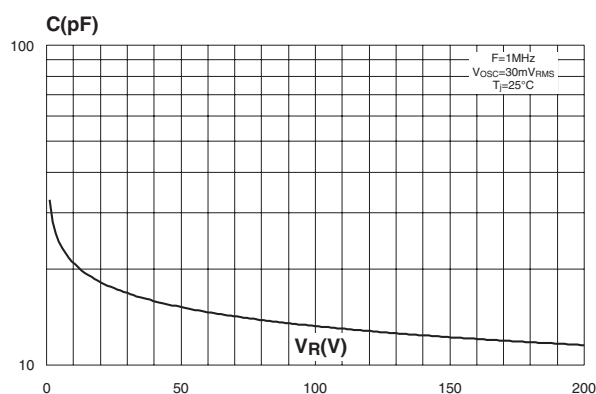
\*\*  $t_p = 380\mu\text{s}$ ,  $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

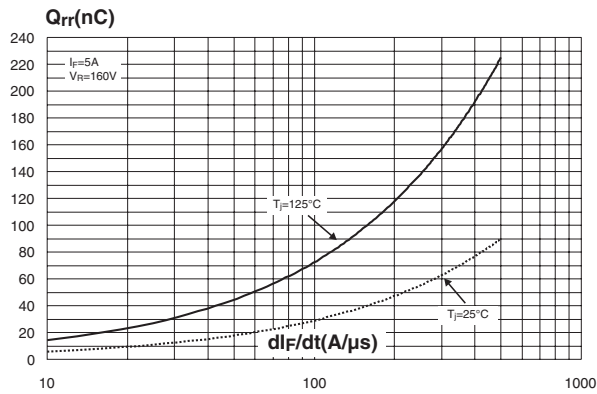
$$P = 0.73 \times I_{F(AV)} + 0.032 I_{F(RMS)}^2$$

### DYNAMIC ELECTRICAL CHARACTERISTICS

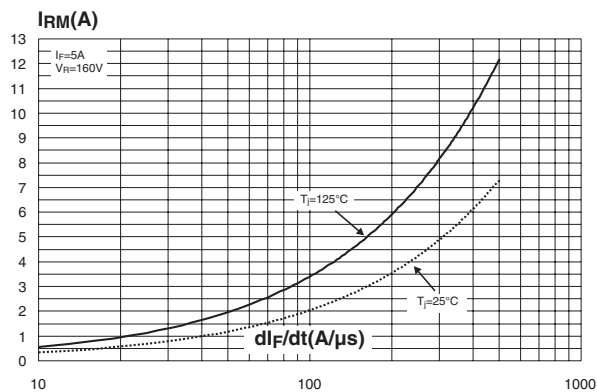
| Symbol   | Parameter                | Tests conditions          |                                                                                           | Min. | Typ. | Max. | Unit |
|----------|--------------------------|---------------------------|-------------------------------------------------------------------------------------------|------|------|------|------|
| $t_{rr}$ | Reverse recovery time    | $T_j = 25^\circ\text{C}$  | $I_F = 1\text{ A}$ $V_R = 30\text{V}$<br>$di_F/dt = 100\text{ A}/\mu\text{s}$             |      | 20   | 25   | ns   |
| $I_{RM}$ | Reverse recovery current | $T_j = 125^\circ\text{C}$ | $I_F = 5\text{ A}$ $V_R = 160\text{V}$<br>$di_F/dt = 200\text{ A}/\mu\text{s}$            |      | 5.9  | 7.6  | A    |
| $t_{fr}$ | Forward recovery time    | $T_j = 25^\circ\text{C}$  | $I_F = 5\text{ A}$ $di_F/dt = 100\text{ A}/\mu\text{s}$<br>$V_{FR} = 1.1 \times V_{Fmax}$ |      |      | 110  | ns   |
| $V_{FP}$ | Forward recovery voltage | $T_j = 25^\circ\text{C}$  | $I_F = 5\text{ A}$ $di_F/dt = 100\text{ A}/\mu\text{s}$                                   |      | 2.4  |      | V    |

**Fig. 1:** Peak current versus duty cycle (per diode).**Fig. 2-1:** Forward voltage drop versus forward current (typical values, per diode).**Fig. 2-2:** Forward voltage drop versus forward current (maximum values, per diode).**Fig. 3-1:** Relative variation of thermal impedance junction to case versus pulse duration (TO-220AB, I<sup>2</sup>PAK, D<sup>2</sup>PAK, DPAK).**Fig. 3-2:** Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAB).**Fig. 4:** Junction capacitance versus reverse voltage applied (typical values, per diode).

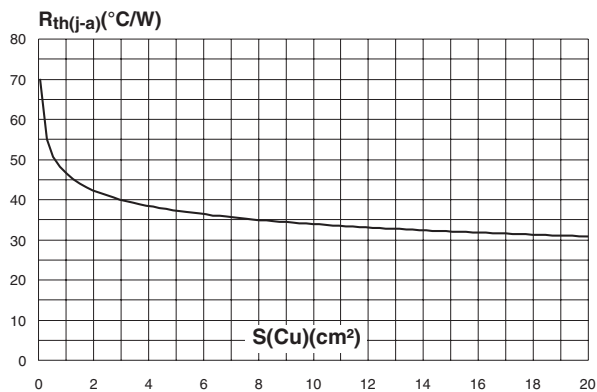
**Fig. 5:** Reverse recovery charges versus  $dl_F/dt$  (typical values, per diode).



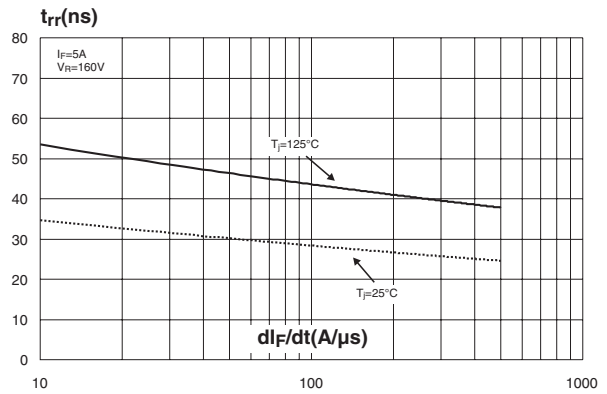
**Fig. 7:** Peak reverse recovery current versus  $dl_F/dt$  (typical values, per diode).



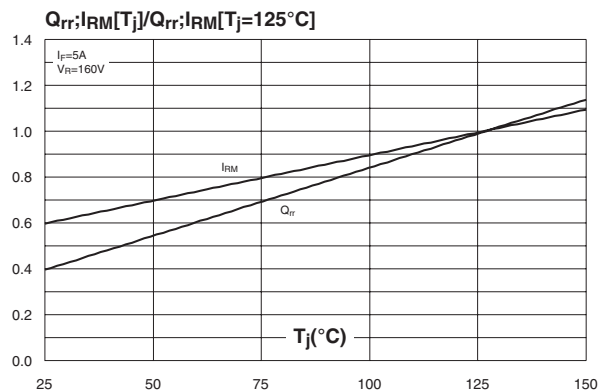
**Fig. 9-1:** Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4,  $e_{Cu}$ : 35μm) for D<sup>2</sup>PAK.



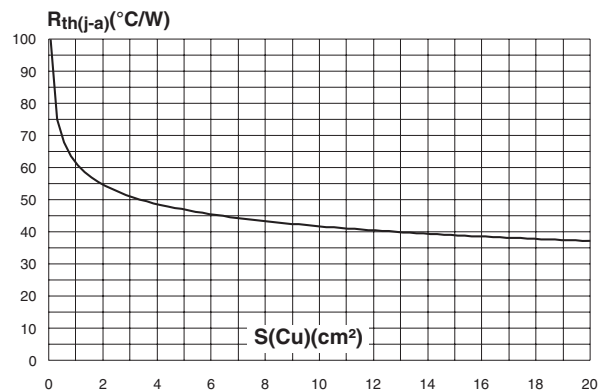
**Fig. 6:** Reverse recovery time versus  $dl_F/dt$  (typical values, per diode).



**Fig. 8:** Dynamic parameters versus junction temperature.



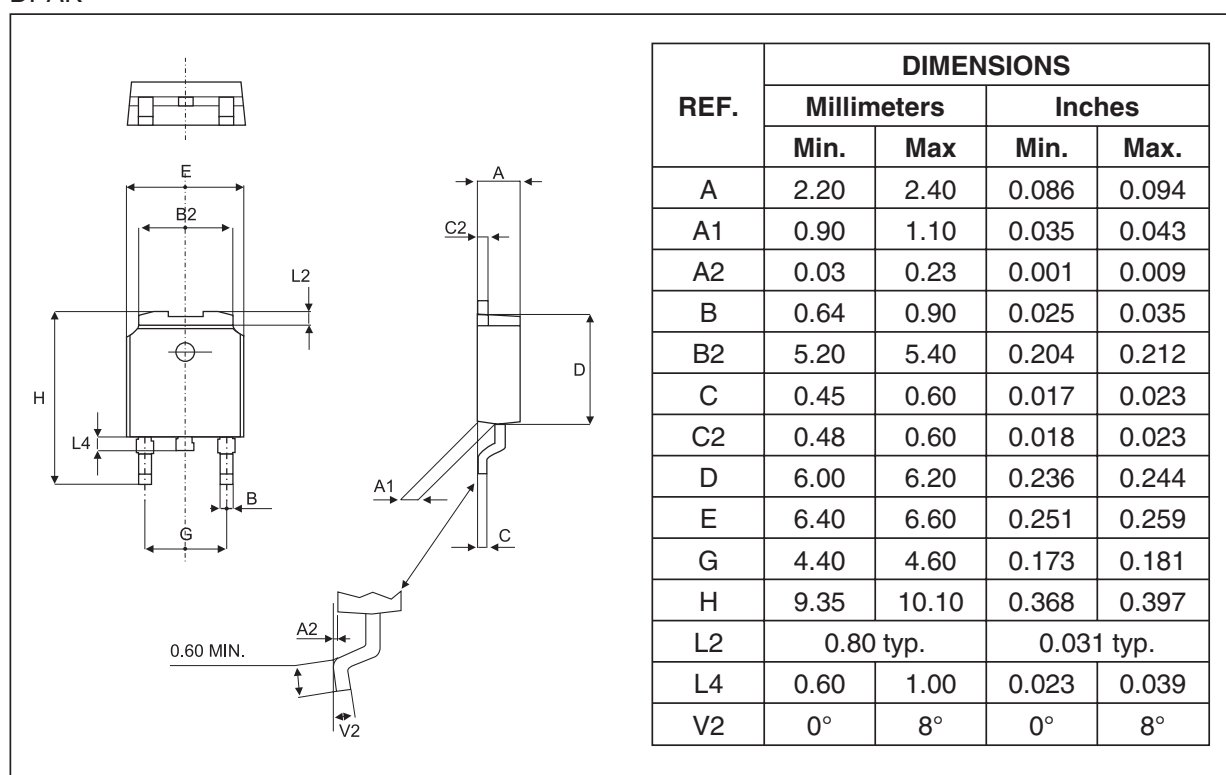
**Fig. 9-2:** Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4,  $e_{Cu}$ : 35μm) for DPAK.



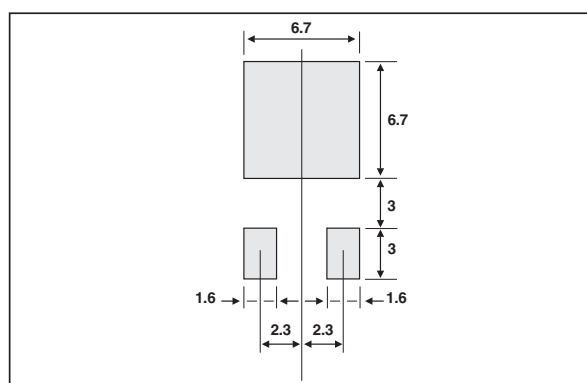
| Ordering code | Marking     | Package            | Weight | Base qty | Delivery mode |
|---------------|-------------|--------------------|--------|----------|---------------|
| STTH1002CB    | STTH1002CB  | DPAK               | 0.3 g  | 75       | Tube          |
| STTH1002CB-TR | STTH1002CB  | DPAK               | 0.3 g  | 2500     | Tape & reel   |
| STTH1002CT    | STTH1002CT  | TO-220AB           | 2.23 g | 50       | Tube          |
| STTH1002CG    | STTH1002CG  | D <sup>2</sup> PAK | 1.48 g | 50       | Tube          |
| STTH1002CG-TR | STTH1002CG  | D <sup>2</sup> PAK | 1.48g  | 1000     | Tape & reel   |
| STTH1002CR    | STTH1002CR  | I <sup>2</sup> PAK | 1.49 g | 50       | Tube          |
| STTH1002CFP   | STTH1002CFP | TO-220FPAB         | 1.70 g | 50       | Tube          |

## PACKAGE MECHANICAL DATA

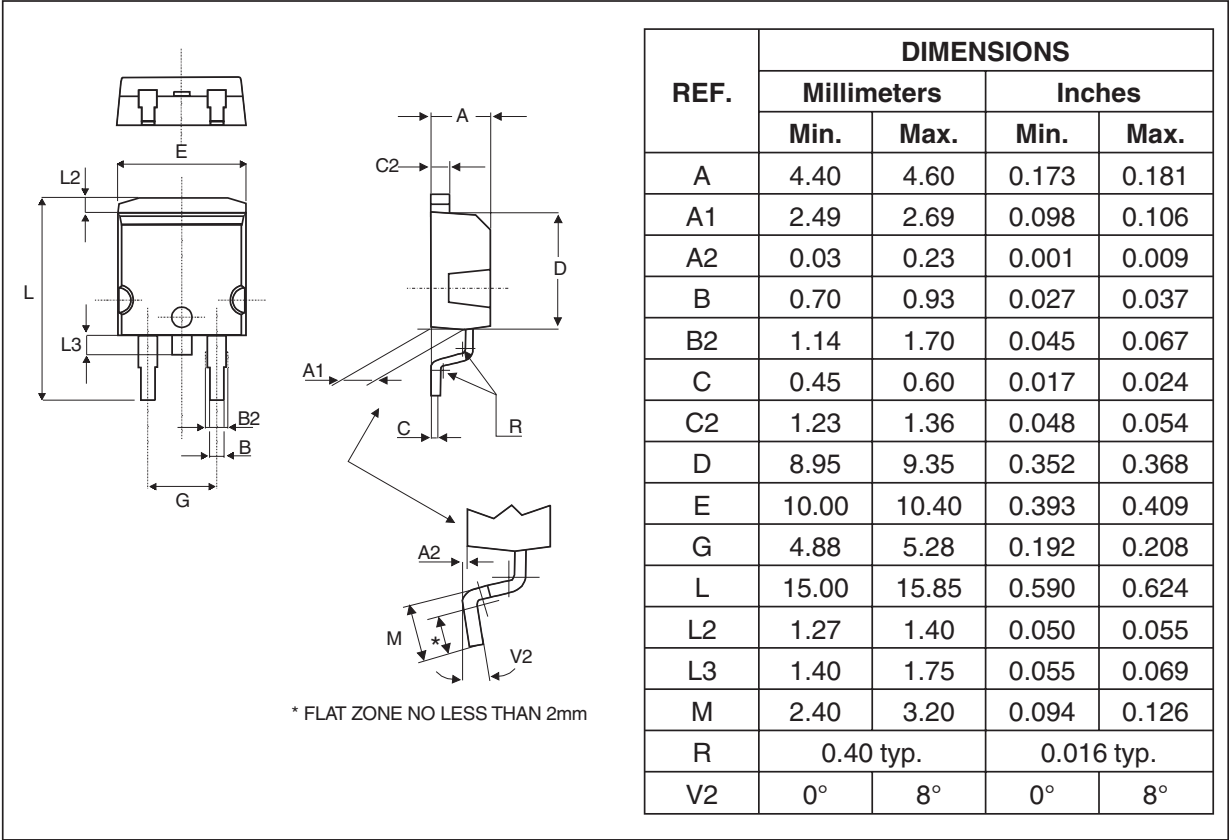
### DPAK



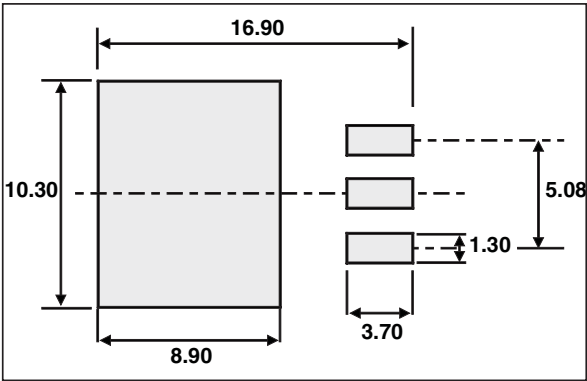
## FOOTPRINT

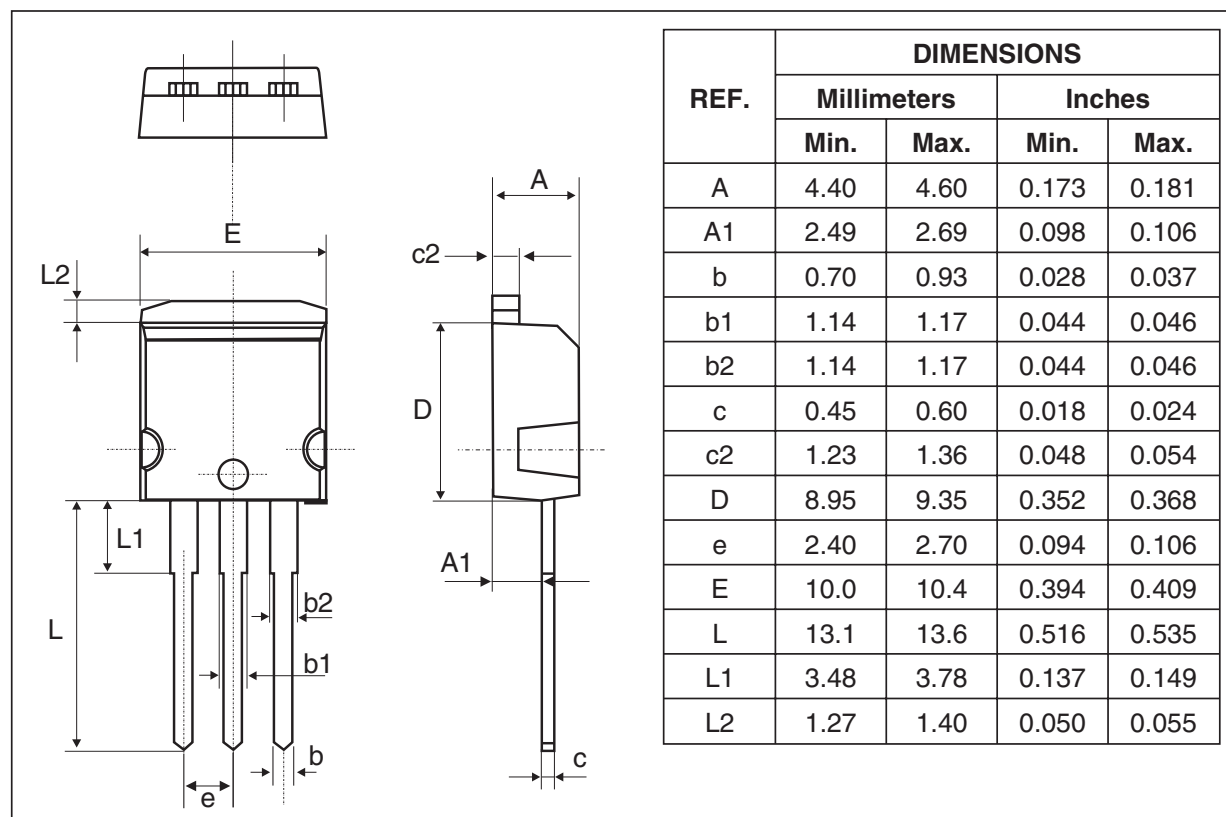
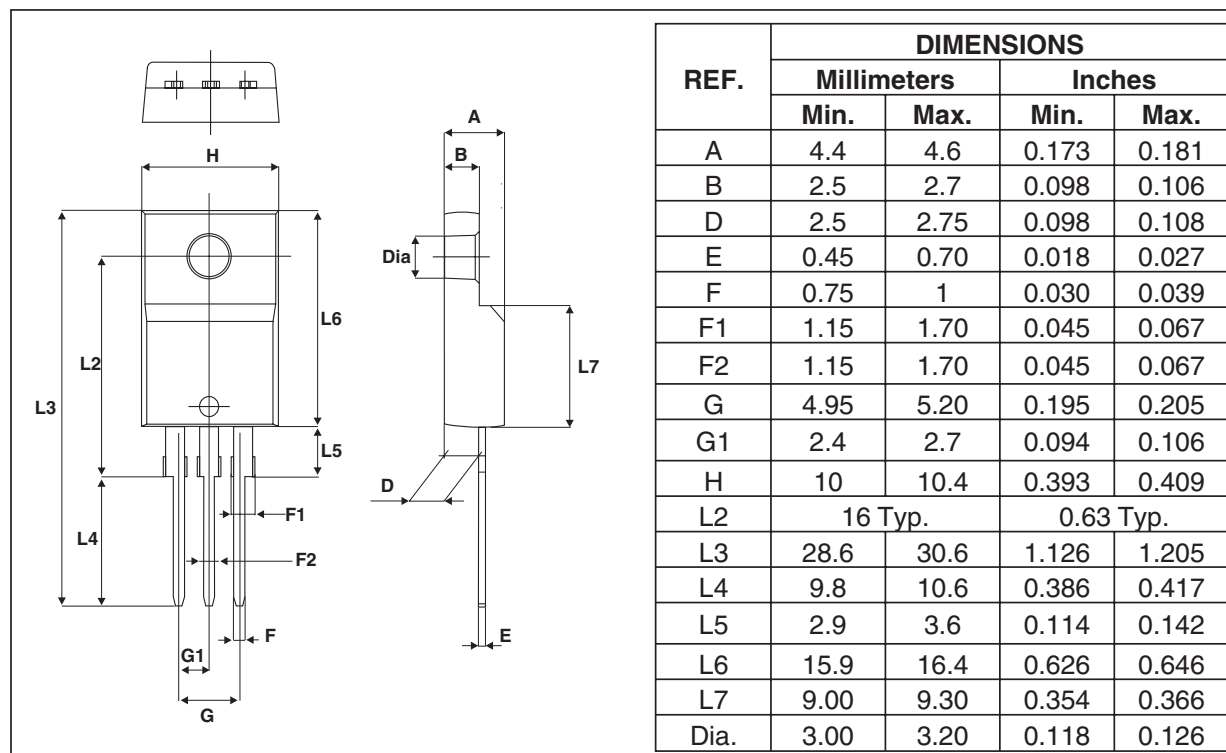


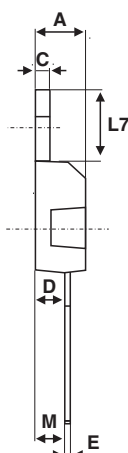
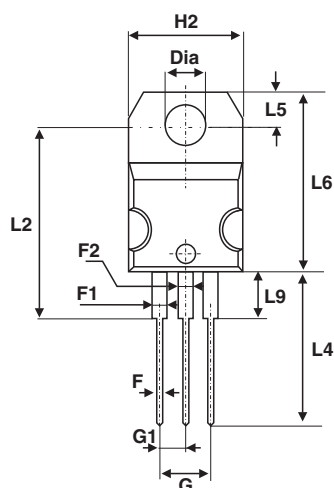
PACKAGE MECHANICAL DATA  
D<sup>2</sup>PAK



FOOTPRINT DIMENSIONS (in millimeters)



**PACKAGE MECHANICAL DATA**  
**I<sup>2</sup>PAK**

**PACKAGE MECHANICAL DATA**  
**TO-220FPAB**


**PACKAGE MECHANICAL DATA**  
**TO-220AB**


| REF.  | DIMENSIONS  |       |            |       |
|-------|-------------|-------|------------|-------|
|       | Millimeters |       | Inches     |       |
|       | Min.        | Max.  | Min.       | Max.  |
| A     | 4.40        | 4.60  | 0.173      | 0.181 |
| C     | 1.23        | 1.32  | 0.048      | 0.051 |
| D     | 2.40        | 2.72  | 0.094      | 0.107 |
| E     | 0.49        | 0.70  | 0.019      | 0.027 |
| F     | 0.61        | 0.88  | 0.024      | 0.034 |
| F1    | 1.14        | 1.70  | 0.044      | 0.066 |
| F2    | 1.14        | 1.70  | 0.044      | 0.066 |
| G     | 4.95        | 5.15  | 0.194      | 0.202 |
| G1    | 2.40        | 2.70  | 0.094      | 0.106 |
| H2    | 10          | 10.40 | 0.393      | 0.409 |
| L2    | 16.4 typ.   |       | 0.645 typ. |       |
| L4    | 13          | 14    | 0.511      | 0.551 |
| L5    | 2.65        | 2.95  | 0.104      | 0.116 |
| L6    | 15.25       | 15.75 | 0.600      | 0.620 |
| L7    | 6.20        | 6.60  | 0.244      | 0.259 |
| L9    | 3.50        | 3.93  | 0.137      | 0.154 |
| M     | 2.6 typ.    |       | 0.102 typ. |       |
| Diam. | 3.75        | 3.85  | 0.147      | 0.151 |

- Epoxy meets UL94,V0
- Cooling method: by conduction (method C)
- Recommended torque value (TO-220AB): 0.8 N.m.
- Maximum torque value (TO-220AB): 1.0 N.m.
- Recommended torque value (TO-220FPAB): 0.55 N.m.
- Maximum torque value (TO-220FPAB): 0.7 N.m.

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